TOSHIBA Diode Silicon Epitaxial Planar Type

1SS314

VHF Tuner Band Switch Applications

Unit: mm

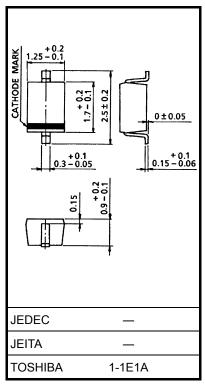
- · Small package.
- Small total capacitance: $C_T = 1.2 pF (max)$
- Low series resistance: $r_s = 0.5 \Omega$ (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V_{R}	30	٧
Forward current	lF	100	mA
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	−55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.004 g (typ.)

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Forward voltage	V_{F}	I _F = 2 mA	_	_	0.85	V
Reverse current	I _R	V _R = 15 V	_	_	0.1	μА
Reverse voltage	V_{R}	$I_R = 1 \mu A$	30	_	_	V
Total capacitance	C _T	V _R = 6 V, f = 1 MHz	_	0.7	1.2	pF
Series resistance	r _S	I _F = 2 mA, f = 100 MHz	_	0.5	0.9	Ω

Marking



